

Charge-Transfer Engineering at Polar Double-Perovskite/Perovskite Interfaces

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In the epitaxy of complex oxides, interfacial charge-transfer phenomena are a promising pathway to engineer functionalities that are absent in the bulk, the discovery of a two-dimensional electron liquid at the interface between LaAlO₃ and SrTiO₃ (STO) being a prominent example [1]. In this context, advanced approaches to manipulate the electronic state of a buried interface are thus very intriguing.

Here, first, we demonstrate that at the interface between a polar double perovskite (La₂NiMnO₆, LNMO) and a non-polar single perovskite (STO), a charge transfer triggered by a polarity mismatch arises. LNMO is a ferromagnetic insulator with a bulk Curie temperature (T_C) around 280 K, resulting from positive superexchange between the long-range-ordered Ni²⁺ and Mn⁴⁺ cations. Bulk-like behavior is well reproduced in high-quality epitaxial films [2]. Nevertheless, the electron doping induced by the electronic reconstruction perturbs the magnetism of the ultrathin LNMO films via formation of Mn³⁺, resulting in a strong reduction of T_C .

To recover the optimal electronic configuration of the buried LNMO//STO interface, we design a top-interface engineering approach through a LaNiO₃ (LNO) overlayer. The presence of LNO is fundamental in displacing the interfacial charge and allows to re-establish the ferromagnetism in LNMO. The LNO-induced electron migration is also obtained on polar LNMO//LSAT interfaces, suggesting that a similar method can be adapted to other polar oxide interfaces [3].

References

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